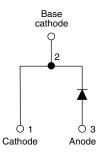
VS-HFA06PB120-N3

Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 6 A



www.vishay.com



PRIMARY CHARACTERISTICS				
I _{F(AV)}	6 A			
V _R	1200 V			
V _F at I _F	2.4 V			
t _{rr} typ.	26 ns			
T _J max.	150 °C			
Package	TO-247AC 2L			
Circuit configuration	Single			

FEATURES

- Ultrafast and ultrasoft recovery
- Very low ${\rm I}_{\rm RRM}$ and ${\rm Q}_{\rm rr}$
- Designed and qualified according to ${\sf JEDEC}^{\circledast}{\sf -JESD}$ 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA06PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V _R		1200	V	
Maximum continuous forward current	I _F	T _C = 100 °C	6		
Single pulse forward current	I _{FSM}	t _p = 10 ms	80	А	
Maximum repetitive forward current	I _{FRM}		24		
Maximum navier discipation	P _D	T _C = 25 °C	62.5	W	
Maximum power dissipation		T _C = 100 °C	25	vv	
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	٥°	

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1

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SHAY

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ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-	
Maximum forward voltage V _{FM}	I _F = 6.0 A	-	2.7	3.0	v	
	V _{FM}	I _F = 12 A	-	3.5	3.9	
		I _F = 6.0 A, T _J = 125 °C	-	2.4	2.8	
Maximum reverse	V _R = V _R rated	-	0.26	5.0		
leakage current		T_J = 125 °C, V_R = 0.8 x V_R rated	-	110	500	μA
Junction capacitance	CT	V _R = 200 V		9.0	14	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH

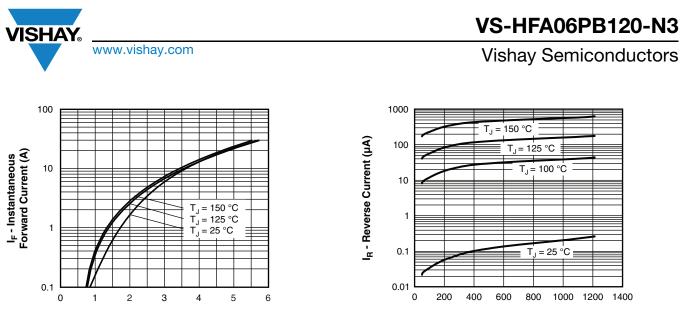
DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	26	-	
Reverse recovery time	t _{rr1}	T _J = 25 °C	I _F = 6.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	53	80	ns
	t _{rr2}	T _J = 125 °C		-	87	130	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.4	8.0	A
	I _{RRM2}	T _J = 125 °C		-	5.0	9.0	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	116	320	
	Q _{rr2}	T _J = 125 °C		-	233	585	ne
Peak rate of recovery current during $t_{\rm b}$	dl _{(rec)M} /dt1	T _J = 25 °C]	-	180	-	A/µs
	dl _{(rec)M} /dt2	T _J = 125 °C		-	100	-	Avµs

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	2.0	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC 2L	HFA06PB120			

Revision: 29-Nov-2019

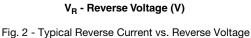
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V_F - Forward Voltage Drop (V)

Fig. 1 - Typical Forward Voltage Drop Characteristics



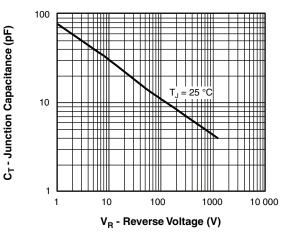


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

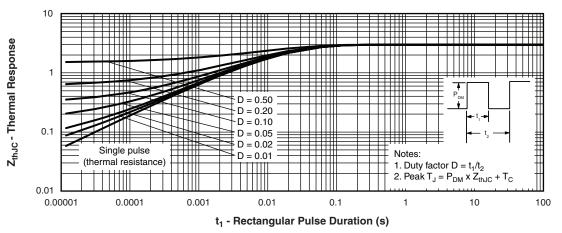


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

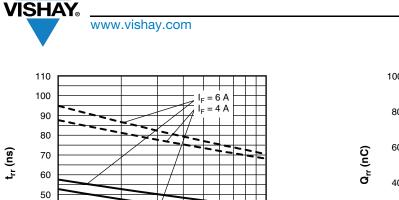


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

40

I_{rr} (A)

100

 $\begin{array}{c} 30 \\ 30 \\ 20 \end{array} \begin{array}{c} V_{R} = 200 V \\ T_{J} = 125 \ ^{\circ}C \\ T_{J} = 25 \ ^{\circ}C \end{array}$

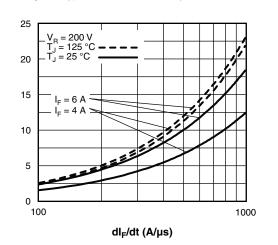


Fig. 6 - Typical Recovery Current vs. dl_F/dt

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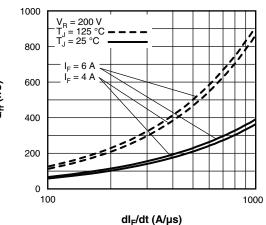


Fig. 7 - Typical Stored Charge vs. dl_F/dt

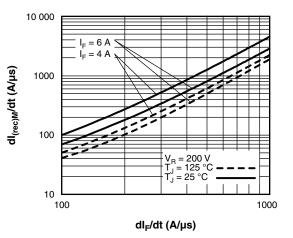
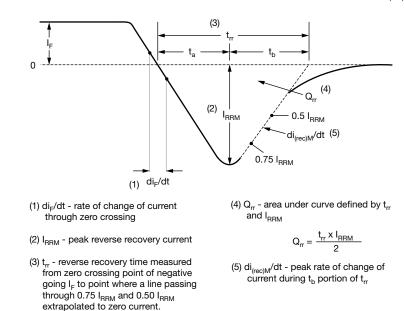
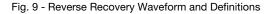


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

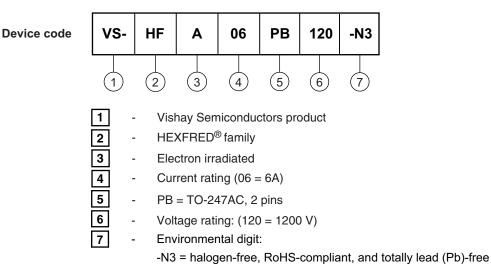




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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-HFA06PB120-N3	25	500	Antistatic plastic tube		

LINKS TO RELATED DOCUMENTS			
Dimensions www.vishay.com/doc?96144			
Part marking information	www.vishay.com/doc?95648		





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